EC2620TTS-33.333M



Series -RoHS Compliant (Pb-free) 3.3V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Temperature Cycling

Vibration

T TS -33.333M EC26 20

Nominal Frequency 33.333MHz

- Pin 1 Connection Tri-State (High Impedance)

- Duty Cycle

Operating Temperature Range --10°C to +70°C

Frequency Tolerance/Stability ±20ppm Maximum 50 ±5(%)

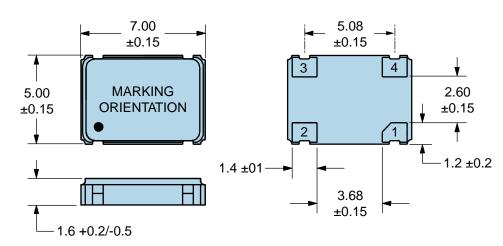
Nominal Frequency 33.333MHz Frequency Tolerance/Stability ±20ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability ov Operating Temperature Range Operating Temperature Range +10°C to +70°C Supply Voltage 3.3Vdc ±10% Input Current 18mA Maximum Output Voltage Logic High (Voh) 90% of Vdd Minimum (IOL=+8mA) Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA) Output Voltage Logic Low (Vol) 10% of Vdd Maximum (IOL=+8mA) Duty Cycle 50 ±5(%) (Measured at 50% of waveform) Load Drive Capability 30pF Maximum Output Logic Type CMOS Pin 1 Connection Tri-State (High Impedance) Tri-State Input Voltage (Vih and Vil) +0.7Vdd Minimum or No Connect to Enable Output, +0.3Vdd Maximum to Disable Output (High Impedance) Standby Current 10µA Maximum (12kHz to 20MHz offset frequency) Start Up Time 10mSec Maximum Storage Temperature Range -55°C to +125°C ENVIRONMENTAL & MECHANICAL SPECIFICATIONS ESD Susceptibility Frest MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
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ESD Susceptibility MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test MIL-STD-883, Method 1014, Condition A	
Flammability UL94-V0	
Gross Leak Test MIL-STD-883, Method 1014, Condition C	
Mechanical Shock MIL-STD-883, Method 2002, Condition B	
Moisture Resistance MIL-STD-883, Method 1004	
Moisture Sensitivity J-STD-020, MSL 1	
Resistance to Soldering Heat MIL-STD-202, Method 210, Condition K	
Resistance to Solvents MIL-STD-202, Method 215	
Solderability MIL-STD-883, Method 2003	_

MIL-STD-883, Method 1010, Condition B

MIL-STD-883, Method 2007, Condition A

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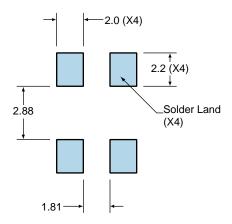
MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Ground/Case Ground
3	Output
4	Supply Voltage
	MARKING
LINE 1	MARKING ECLIPTEK

Suggested Solder Pad Layout

All Dimensions in Millimeters



All Tolerances are ±0.1



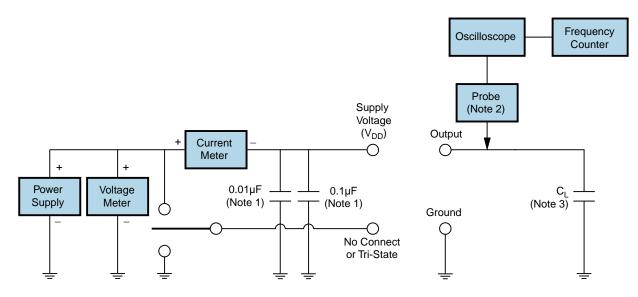
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OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



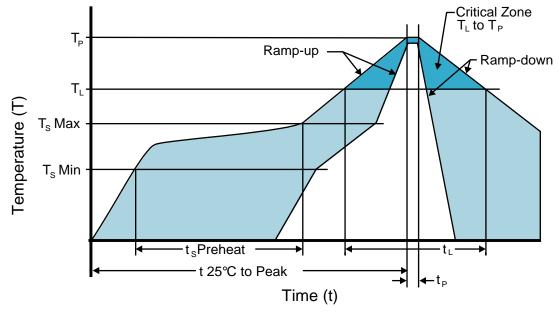
Note 1: An external 0.1μ F low frequency tantalum bypass capacitor in parallel with a 0.01μ F high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_L includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

EC2620TTS-33.333M

T_s MAX to T_L (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	150°C
 Temperature Typical (T_s TYP) 	175°C
 Temperature Maximum (T_s MAX) 	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (t _p)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods

EC2620TTS-33.333M



Low Temperature Infrared/Convection 240°C

T_s MAX to T_L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _s TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (t _p)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)